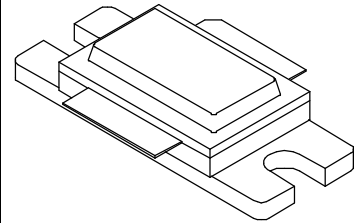


GENERAL DESCRIPTION

The **TAN350** is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 960-1215 MHz. The device has gold thin-film metallization and diffused ballasting for proven highest MTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

CASE OUTLINE 55ST Style 1



ABSOLUTE MAXIMUM RATINGS

Power Dissipation

Device Dissipation @25°C (P_d) 1450 W (At rated pulse condition)

Voltage and Current

Collector to Base Voltage (BV_{ces}) 65 V

Emitter to Base Voltage (BV_{ebo}) 2.0 V

Collector Current (I_c) 40 A

Temperatures

Storage Temperature -65 to +200 °C

Operating Junction Temperature +230 °C

ELECTRICAL CHARACTERISTICS @ 25°C

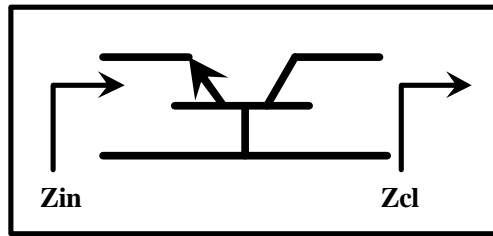
SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P_{out}	Power Out	F = 960 – 1215 MHz	350			W
P_{in}	Power Input	$V_{CC} = 50$ Volts			70	W
P_g	Power Gain	PW = 10 μ sec	7.0	7.5		dB
η_c	Collector Efficiency	DF = 10%	38	40		%
VSWR	Load Mismatch Tolerance	F = 1090 MHz	3:1			

FUNCTIONAL CHARACTERISTICS @ 25°C

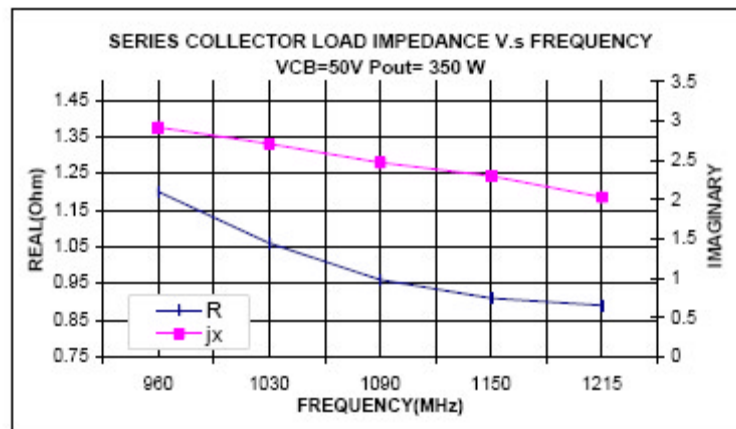
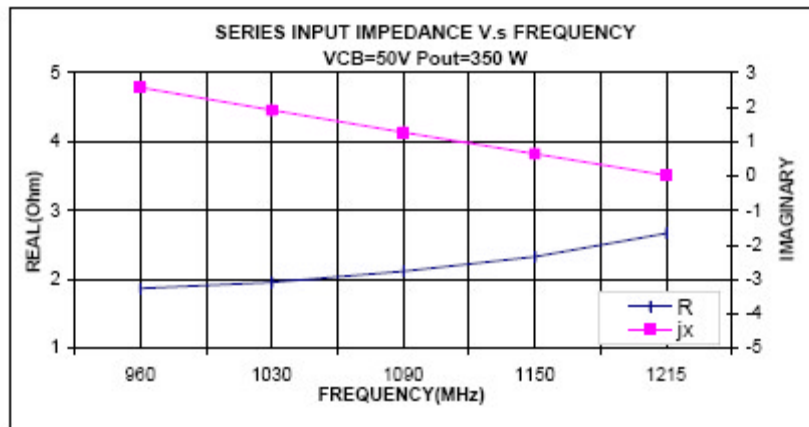
BV_{ebo}	Emitter to Base Breakdown	$I_e = 25$ mA	2.0			V
BV_{ces}	Collector to Emitter Breakdown	$I_c = 50$ mA	65			V
h_{FE}	DC – Current Gain	$I_c = 1A$, $V_{ce} = 5V$	10			
θ_{jc}^2	Thermal Resistance			.12		°C/W

Rev A - Sept. 2005

Frequency	Zin		ZCL	
	R	jx	R	jx
960	1.87	2.58	1.2	2.92
1030	1.96	1.92	1.06	2.71
1090	2.12	1.27	0.96	2.47
1150	2.33	0.65	0.91	2.3
1215	2.67	0.03	0.89	2.03

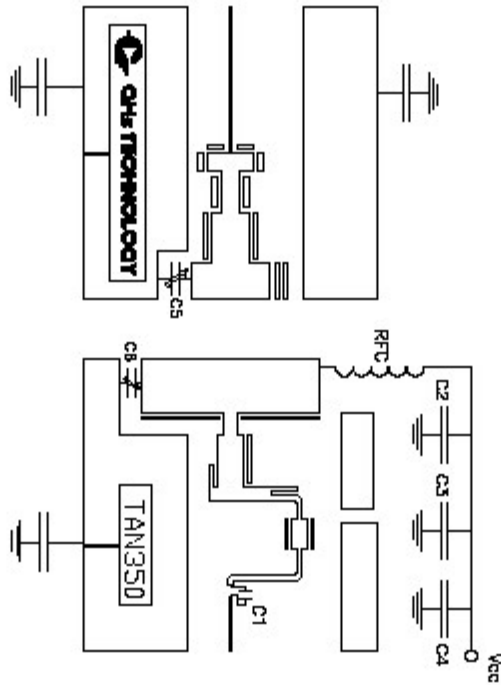


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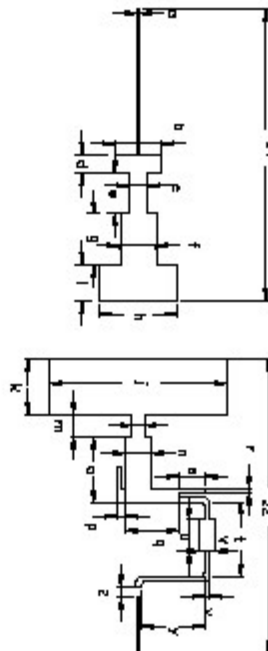


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1. ONLY THE ITEM DESCRIBED ON THIS DRAWING WHEN PRODUCE FROM THE APPROVED SUPPLIER LIST, IS APPROVED FOR USE IN THE APPLICATION SPECIFIED HEREON. A SUBSTITUTE ITEM SHALL NOT BE USED WITHOUT PRIOR TESTING AND APPROVAL BY GHT.



	Dim.	inches	Dim.	inches
d	.033	n	.175	
b	.323	o	.450	
c	.127	p	.080	
e	.125	q	.384	
d	.278	r	.030	
f	.247	s	.177	
g	.345	t	.507	
h	.547	u	.215	
i	.253	v	.100	
j	1.210	x	.037	
k	.370	y	.435	
l	.084	z	.070	
m	.152	z1,z2	2.000	



NOTES, UNLESS OTHERWISE SPECIFIED:

- ONLY THE ITEM DESCRIBED ON THIS DRAWING WHEN PRODUCED FROM THE "APPROVED SUPPLIER LIST" IS APPROVED FOR USE IN THE APPLICATION SPECIFIED HEREON. A SUBSTITUTE ITEM SHALL NOT BE USED WITHOUT PRIOR TESTING AND APPROVAL BY GHS.

DIM	inches	DIM	inches
a	.0033	n	.175
b	.323	o	.450
c	.137	p	.080
d	.125	q	.364
e	.278	r	.030
f	.247	s	.177
g	.345	t	.507
h	.5417	u	.215
i	.253	v	.100
j	1.210	x	.037
k	.370	y	.435
l	.084	z	.020
m	.152	z1, z2	2.000

THE DRAWING SHALL BE USED IN CONJUNCTION WITH THE SPECIFICATIONS AND THE INSTRUCTIONS OF THE MANUFACTURER. THE USER SHALL BE RESPONSIBLE FOR THE PROPER USE OF THE PRODUCT. THE MANUFACTURER SHALL BE RESPONSIBLE FOR THE PROPER USE OF THE PRODUCT. THE MANUFACTURER SHALL BE RESPONSIBLE FOR THE PROPER USE OF THE PRODUCT.

GHX TECHNOLOGY

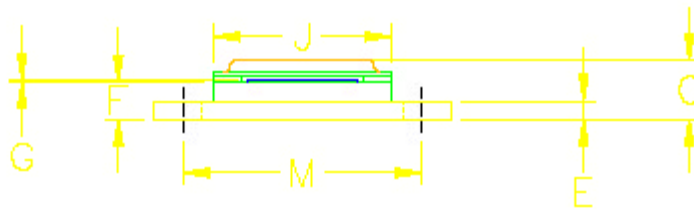
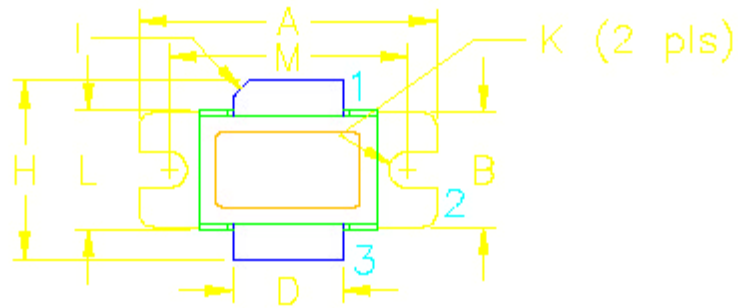
2000 DAKOTA VALLEY DRIVE
BETH COLE, VA 20001-0800

TAN 350

SIZE: A
CASE CODE: 0PJR2
DEC/1997 MFG: TAN 350
SHEET: 4 OF 5

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TAN350

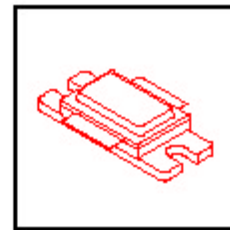


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DIM	MILLIMETER	±TOL	INCHES	±TOL
A	25.40	.25	1.000	.010
B	9.78	.25	.385	.010
C	4.00	.19	.142	.007
D	9.40	.13	.370	.005
E	1.53	.13	.060	.005
F	3.18	.13	.125	.005
G	0.08	+0.05/-0.00	.003	+0.002/-0.000
H	19.05	0.51	.750	.020
I	45°	5°	45°	5°
J	15.24	.25	.600	.010
K	3.05 DIA	.13	.120 DIA	.005
L	10.15	.13	.400	.005
M	20.32	.25	.800	.010

STYLE 1:
PIN 1 = COLLECTOR
2 = BASE
3 = EMITTER

STYLE 2:
PIN 1 = COLLECTOR
2 = EMITTER
3 = BASE



DWG NO.

55ST

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